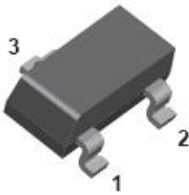


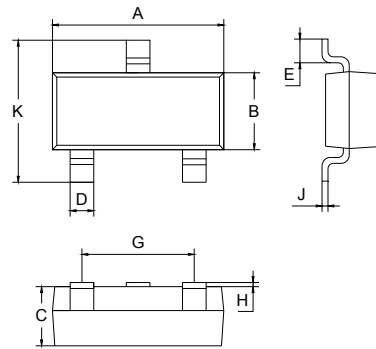
FEATURES

- High current gain bandwidth product.
- Power dissipation.($P_c=200\text{mW}$).



APPLICATIONS

- NPN epitaxial silicon transistor.



SOT-23		
Dim	Min	Max
A	2.70	3.10
B	1.10	1.50
C	1.0 Typical	
D	0.4 Typical	
E	0.35	0.48
G	1.80	2.00
H	0.02	0.1
J	0.1 Typical	
K	2.20	2.60
All Dimensions in mm		

ORDERING INFORMATION

Type No.	Marking	Package Code
S9018	J8	SOT-23

MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	25	V
V_{CEO}	Collector-Emitter Voltage	18	V
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current -Continuous	50	mA
P_C	Collector Dissipation	200	mW
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$

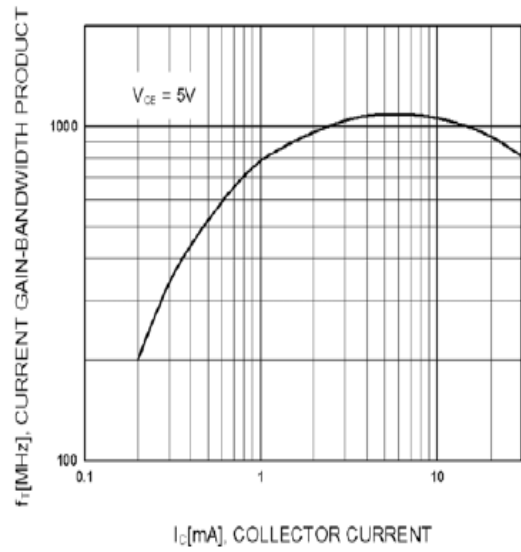
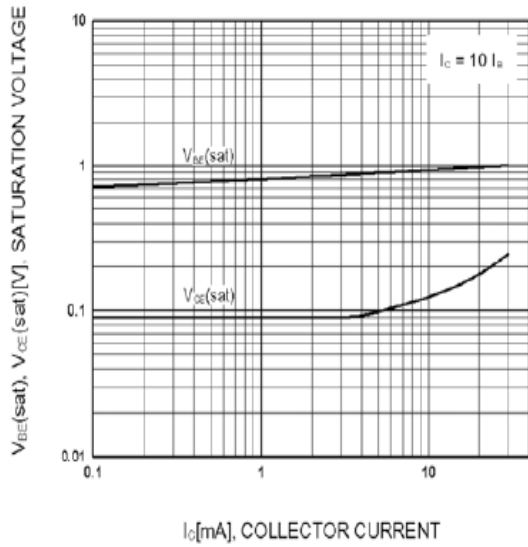
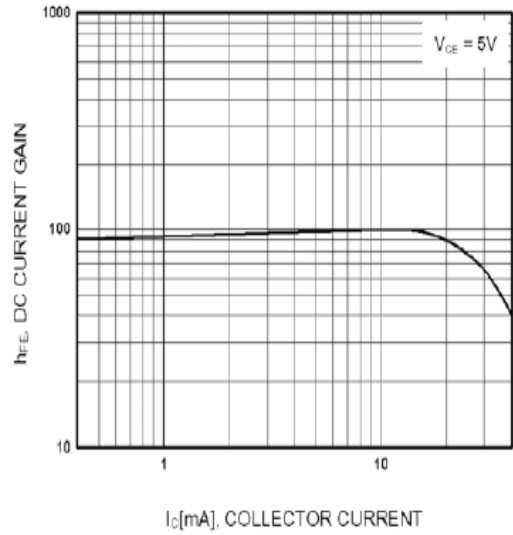
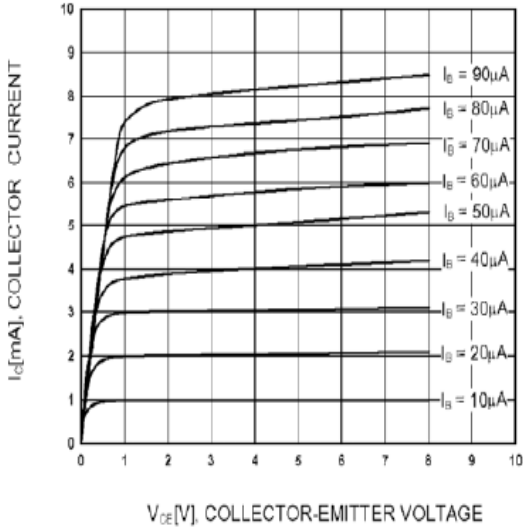


ELECTRICAL CHARACTERISTICS @ Ta=25 °C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=0.1mA, I_B=0$	18			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	4			V
Collector cut-off current	I_{CBO}	$V_{CB}=20V, I_E=0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=15V, I_B=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=3V, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=5V, I_C=1mA$	70		190	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=1mA$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=10mA, I_B=1mA$			1.4	V
Transition frequency	f_T	$V_{CE}=5V, I_C=5mA$ $f=400MHz$	600			MHz



TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



Device	Package	Shipping
S9018	SOT-23	3000/Tape&Reel